

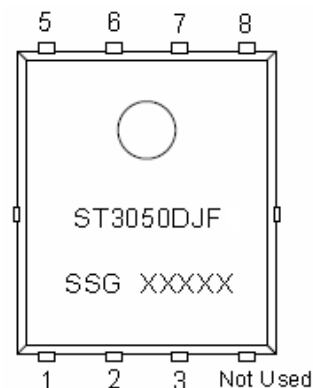
ST3050DJF POWER SCHOTTKY RECTIFIER

Applications:

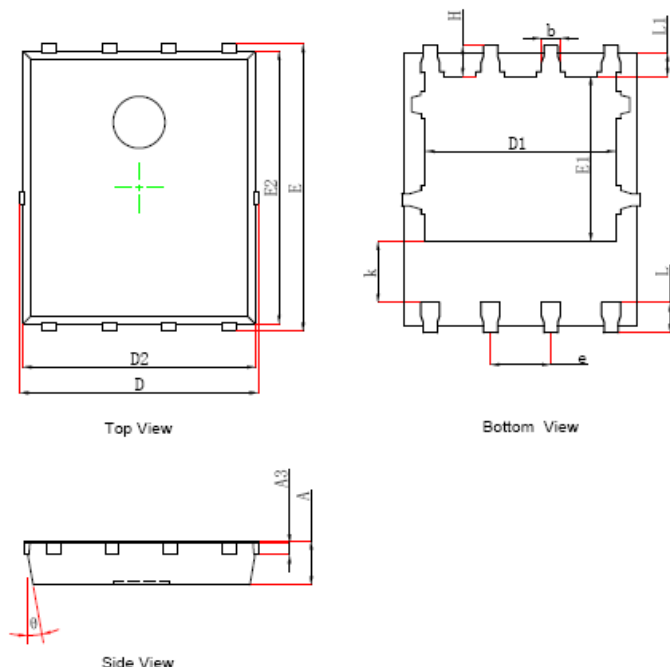
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- Ultralow forward voltage drop
- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Low thermal resistance
- Avalanche capability specified
- Thin package: 1 mm
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



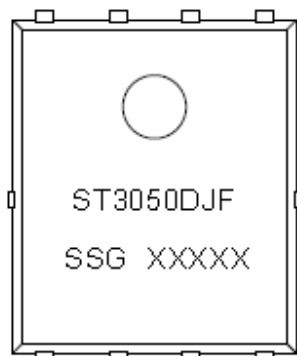
Mechanical Dimensions: In mm/Inches



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

PDFNWB5×6-8L

Marking Diagram:



Where XXXXX is YYWWL

ST = Device Type
 30 = Forward Current (30A)
 50 = Reverse Voltage (50V)
 DJF = Package type
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL: 94V-0

Ordering Information:

Device	Package	Shipping
ST3050DJF	PDFNWB5x6-8L (Pb-Free)	3000 pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	50	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 80^\circ\text{C}$, rectangular wave form	30	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	180	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 5A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.32	-	V
		@ 10A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.37	-	
		@ 15A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.47	0.50	
		@ 30A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.57	0.60	
	V_{F2}	@ 5A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.25	-	V
		@ 10A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.33	-	
		@ 15A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.39	0.45	
Reverse Current *	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	-	0.8	mA
		@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	-	60	mA

* Pulse Width < 300 μ s, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-	-65 to + 175	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	2.6	$^\circ\text{C/W}$
Approximate Weight	wt	-	0.095	g
Case Style	PDFNWB5x6-8L			

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